In the claims:

Please amend the claims as follows:

Claim 15. (Currently Amended) An etching method using a dry etching apparatus provided with ~~at least first, second and third electrodes, said first~~ an upper electrode and a lower electrode being opposed to said ~~second and third~~ upper electrode ~~electrodes~~, said lower electrode comprising at least first and second electrodes, said upper electrode comprising one coil electrode overlapped with said first and second electrodes, the method comprising the steps of:

disposing a substrate on said first and second ~~and third~~ electrodes in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to said coil electrode;

applying a ~~first~~ second high-frequency power to said ~~second~~ first electrode disposed below a central portion of said substrate and applying a ~~second~~ third high-frequency power to said ~~third~~ second electrode disposed below corner portions of said substrate to supply an AC electric field between said ~~first~~ coil electrode and said first and second ~~and third~~ electrodes;

generating plasma between said ~~first~~ electrode and said first and second ~~and third~~ electrodes; and

etching a material film on said substrate disposed on said first and second ~~and third~~ electrodes,

wherein said second electrode is flush with said ~~third~~ first electrode.

Claim 16. (Currently Amended) An etching method according to claim 15, wherein a frequency of each of said first, second, and third high-frequency power is the same ~~as that of said second high-frequency power~~.

Claim 17. (Currently Amended) An etching method according to claim 15, wherein said dry etching apparatus is ~~a parallel-plate etching apparatus or~~ an ICP-type etching apparatus.

Claim 18. (Currently Amended) An etching method using a dry etching apparatus, the method comprising the steps of:

disposing a substrate on a plurality of electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to a coil electrode opposed to said plurality of electrodes, said coil electrode overlapped with said plurality of electrodes;

applying a ~~first~~ second high-frequency power to an electrode disposed below a central portion of said substrate and applying a ~~second~~ third high-frequency power to electrodes disposed below corner portions of said substrate;

generating plasma with a magnetic field or an electric field between said coil electrode and said plurality of electrodes; and

etching a material film on said substrate disposed on said plurality of electrodes,

wherein said plurality of electrodes are flush with each other.

Claim 19. (Original) An etching method according to claim 18, wherein said dry etching apparatus is one selected from the group consisting of a magnetron-type etching apparatus, an ECR-type etching apparatus, and a helicon-type etching apparatus.

Claim 20. (Currently Amended) A method of forming a wiring, the method comprising the steps of:

forming a conductive film on a substrate;

selectively forming a mask on said conductive film;

disposing said substrate on at least first and second electrodes provided in a chamber provided with a third electrode opposed to said first and second electrodes, said coil electrode overlapped with said first and second electrodes;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to said coil electrode;

applying a ~~first~~ second high-frequency power to said first electrode disposed below a central portion of said substrate and applying a ~~second~~ third high-frequency power to said second electrode disposed below corner portions of said substrate to apply an AC electric field between said ~~third~~ coil electrode and said first and second electrodes;

generating plasma between said third electrode and said first and second electrodes; and

selectively etching said conductive film on said substrate,

wherein said first electrode is flush with said second electrode.

Claim 21. (Original) A method of forming a wiring according to claim 20, wherein said wiring is a gate electrode or a gate wiring of a TFT.

Claim 22. (Currently Amended) An etching method using a dry etching apparatus,

providing at least first~~,~~ and second ~~and third~~ electrodes, and a coil electrode overlapped with said first and second electrodes, the electrodes being independent from each other, said ~~first~~ coil electrode being opposed to said first and second ~~and third~~ electrodes, and at least first, second, and third high-power sources independently connected to each of said first, second and ~~third~~ coil electrodes, respectively, the method comprising the steps of:

disposing a substrate on said first and second ~~and third~~ electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

generating plasma between said ~~first~~ coil electrode and said first and second ~~and third~~ electrodes; and

etching a material film on said substrate disposed on said first and second ~~and third~~ electrodes,

wherein said first and second ~~and third~~ electrodes are disposed so that an electric power applied to an entire surface of said substrate becomes uniform,

wherein said second electrode is flush with said ~~third~~ first electrode.

Claim 23. (Original) An etching method according to claim 22, wherein the dry etching apparatus is one selected from the group consisting of a magnetron-type etching apparatus, an ECR-type etching apparatus, and a helicon-type etching apparatus.

Claim 24. (Currently Amended) A method of manufacturing a semiconductor device using a dry etching apparatus,

providing at least first~~,~~ and second ~~and third~~ electrodes, and a coil electrode overlapped with said first and second electrodes, the electrodes being independent from each other, said ~~first~~

coil electrode being opposed to said first and second ~~and third~~ electrodes, the method comprising the steps of:

forming a material film on a substrate;

selectively forming a mask on said material film;

disposing said substrate on said first and second ~~and third~~ electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to said coil electrode;

applying a ~~first~~ second high-frequency power to said ~~second~~ first electrode disposed below a central portion of said substrate and applying a ~~second~~ third high-frequency power to said ~~third~~ second electrode disposed below corner portions of said substrate;

generating plasma between said ~~first~~ coil electrode and said first and second ~~and third~~ electrodes; and

etching a material film on said substrate disposed on said first and second ~~and third~~ electrodes,

wherein said second electrode is flush with said ~~third~~ first electrode.

Claim 25. (Original) A method of manufacturing a semiconductor device according to claim 24, wherein said semiconductor device is incorporated into an electronic device selected from the group consisting of a personal computer, a video camera, a mobile computer a goggle type display, a player, a digital camera, a front type projector, a rear type projector, a portable telephone a portable book, and a display.

Claim 26. (Currently Amended) An etching method comprising:

providing a radial line slot antenna supplying a microwave, at least first and second electrodes and at least first and second high-power sources independently connected to each of said first and second electrodes;

disposing a substrate on said first and second electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

generating plasma between said the radial slot antenna and said first and second electrodes by supplying the microwave from said radial slot antenna; and

etching a material film on said substrate disposed on said first and second electrodes,

wherein said first and second electrodes are disposed so that an electric power applied to an entire surface of said substrate becomes uniform,

wherein said first electrode is flush with said second electrode.

Claim 27. (Currently Amended) A method of manufacturing a semiconductor device comprising:

providing a radial line slot antenna supplying a microwave, at least first and second electrodes,

forming a material film on a substrate;

selectively forming a mask on said material film;

disposing said substrate on said first and second electrodes provided in a chamber;

supplying a reaction gas into said chamber under a reduced pressure;

applying a first high-frequency power to said first electrode disposed below a central portion of said substrate and applying a second high-frequency power to said ~~third~~ second electrode disposed below corner portions of said substrate;

generating plasma between said the radial slot antenna and said first and second electrodes by supplying the microwave from said radial slot antenna; and

etching a material film on said substrate disposed on said first and second electrodes,

wherein said first electrode is flush with said second electrode.

Claim 28. (Previously Added) A method of manufacturing a semiconductor device according to claim 27, wherein said semiconductor device is incorporated into an electronic device selected from the group consisting of a personal computer, a video camera, a mobile computer a goggle type display, a player, a digital camera, a front type projector, a rear type projector, a portable telephone a portable book, and a display.

Claim 29. (Currently Amended) An etching method comprising:

providing at least first, second, third, fourth ~~and~~ fifth, and coil electrodes and at least first, second, third, fourth ~~and~~ fifth, and sixth high-power sources independently connected to each of said first, second, third, fourth ~~and~~ fifth, and coil electrodes, said coil electrode overlapped with said first, second, third, fourth, and fifth electrodes;

disposing a substrate on said first, second, third, fourth and fifth electrodes provided in a chamber, wherein said first electrode is located below a central portion of said substrate and second, third, fourth and fifth electrodes are located below corner portions of said substrate;

supplying a reaction gas into said chamber under a reduced pressure;

generating plasma between said first, second, third, fourth, and fifth electrodes and said coil electrode overlapped with said first, second, third, fourth, and fifth electrodes; and

etching a material film on said substrate,

wherein said first, second, third, fourth and fifth electrodes are disposed so that an electric power applied to an entire surface of said substrate becomes uniform, and

wherein said first, second, third, fourth and fifth electrodes are flush with each other.